

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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InGaP HBT 2.4 - 2.5 GHz Power Amplifier Module

PRODUCTION DATA SHEET

DESCRIPTION

The LX5516 is a power amplifier module optimized for applications in the frequency range. The implemented as a two-stage monolithic current. microwave integrated circuit (MMIC) output.

(HBT) IC (MOCVD). With single low voltage 802.11b/g/n applications. supply of 3.3V, it delivers 29dB power gain between 2.4-2.5GHz, at a low quiescent current of 80mA.

For 18dBm OFDM output power WLAN (64QAM, 54Mbps), the PAM provides a 2.4-2.5GHz low EVM (Error-Vector Magnitude) of PAM is 2.5%, and consumes 130mA total DC

The LX5516 is available in a 12-pin with on-chip active bias and 50 Ω 2x2mm micro-lead package (MLPQimpedance matched at both input and 12L). The compact footprint, ultra low profile, and thermal capability of the The device is manufactured with an MLP package make the LX5516 an InGaP/GaAs Heterojunction Bipolar ideal solution for high-gain power process amplifier requirements IEEE

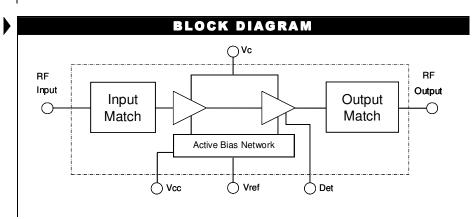
KEY FEATURES

- Advanced InGaP HBT
- 2.4-2.5GHz Operation
- Single-Polarity 3.3V Supply
- Quiescent Current ~80mA
- Power Gain ~ 29 dB
- Pout=~+18dBm for 2.5% EVM, OFDM 64QAM/54Mbps
- Total Current ~130mA for Pout= +18dBm
- 50Ω Input/Output Matching
- On-chip Output Power Detector
- Small Footprint: 2x2mm²
- Ultra Low Profile:0.46mm

APPLICATIONS

■ IEEE 802.11b/g/n

IMPORTANT: For the most current data, consult MICROSEMI's website: http://www.microsemi.com



2X2MM MLP PACKAGE

PACKAGE ORDER INFO

Plastic MLPQ LL 12 pin 2x2mm LX5516LL

Note: Available in Tape & Reel. Append the letters "TR" to the part number. (i.e. LX5516LL-TR)



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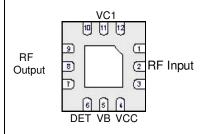
PRODUCTION DATA SHEET

ABSOLUTE MAXIMUM RATINGS

DC Supply Voltage, RF off	5\/
Collector Current	
Total Power Dissipation	
RF Input Power (With 50 Ohm Load at Output)	+10 dBm
Maximum operating Junction Temperature (Tj)	
150℃	
Operation Ambient Temperature	40 to +85℃
Storage Temperature	
Package Peak Temp. for Solder Reflow (40 seconds maximul	m exposure)260 °C (+0
-5)	

Note: Exceeding these ratings could cause damage to the device. All voltages are with respect to Ground. Currents are positive into, negative out of specified terminal.

PACKAGE PIN OUT



LL PACKAGE (Bottom View)

RoHS / Pb-free 100% NiPdAu Lead Finish

THERMAL DATA

Plastic MLPQ 12-Pin

THERMAL RESISTANCE-JUNCTION TO CASE, θ_{JC}	7.9 C/W
THERMAL RESISTANCE-JUNCTION TO AMBIENT, θ_{JA}	76.5 C/W

Junction Temperature Calculation: $T_J = T_A + (P_D \times \theta_{JA})$.

The θ_{JA} numbers are guidelines for the thermal performance of the device/pc-board system. All of the above assume no ambient airflow.

FUNCTIONAL PIN DESCRIPTION	
Name	Description
RF IN (2)	RF input for the power amplifier.
VCC (4)	Supply voltage for the bias reference and control circuits.
VB (5)	Bias control voltage for the first and second stage.
DET(6)	Output power Detector.
RF OUT(8)	RF output and power supply for the second stage amplifier.
VC1(11)	DC supply voltage for the first stage amplifier.
GND	The center metal base of the MLP package provides both DC/RF ground as well as heat sink for the power amplifier.
(1,3,7,9,10, 12)	PINs to be grounded to the center metal on the PCB.



INFORMATION

Thank you for your interest in Microsemi® Analog Mixed Signal products.

The full data sheet for this device contains proprietary information.

To obtain a copy, please contact your local Microsemi sales representative. The name of your local representative can be obtained at the following link http://www.microsemi.com/contact/contactfind.asp

or

Contact us directly by sending an email to:

IPGdatasheets@microsemi.com

Be sure to specify the data sheet you are requesting and include your company name and contact information and or vcard.

We look forward to hearing from you.